

# High Accuracy Current Sensor IC with 1.5MHz 3dB Bandwidth and Isolation ±5A, ±20A, ±50A, 3.3V, Ratiometric



MCR1101-xx-3

#### FEATURES

- AMR based integrated current sensor
- Superior Range & Accuracy 0.6% typical total error @25°C (MCR1101-20-3) 2.0% max error over temperature (MCR1101-20-3)
- Superior Frequency Response
  - 1.5 MHz (typical 3dB BW)
- Fast output response time (300ns typical)
- Low Primary Resistance (0.9 mΩ)
- Single 3.3V Supply Operation
- Low power consumption (4.5mA typical)
- Overcurrent fault detection
- SOIC-16 package (RoHS/REACH compliant)
- -40 to +105°C Operating Temperature Range
- UL/IEC/EN60950-1 Certified

   4.8 kV Dielectric Strength Voltage
   1097 VRMS Basic Isolation Voltage
   400 VRMS Reinforced Isolation Voltage

#### APPLICATIONS

- Server, Telecom, & Industrial Power Supplies Power Aggregation, Over-Current Protection Dynamic Current Sensing in Feedback Loops PFC and Inverter Control
- Motor Control Loops & Protection Automation, Robotics, Servo Systems Automotive & EV Power Systems

**Solar Inverters and Optimizers** 

Grid-Tie and Storage Current Monitoring MPPT Circuit Current Monitoring Central Inverter Current Monitoring

#### Consumer

Motor Balance and Remote Device Monitoring Home Automation Control & IOT remote sensing

#### DESCRIPTION

The MCR1101 products are  $\pm 5A$ ,  $\pm 20A$ ,  $\pm 50A$  fully integrated bi-directional analog output current sensors that deliver both high accuracy and high bandwidth. ACEINNA's state-of-the-art Anisotropic Magneto Resistive (AMR) sensor technology provides inherently low noise, excellent linearity and repeatability.

A fully isolated current path is provided by a low resistance copper conductor integrated into the package making it suitable for both high-side and low side bi-directional current sensing. The high bandwidth of 1.5MHz (3dB) and low phase delay makes it ideal for current sense feedback loops in motor control, inverters, uninterruptible power supplies, battery management, power factor correction, high voltage distribution bus converters and power supply applications, including those with fast switching wide-bandgap SiC and GaN based power stages.

These devices are factory-calibrated to achieve low offset error and provide a precise analog voltage output that is linearly proportional to the conduction current (AC or DC) with sensitivity (mV/A) compatible with A/D converters and analog control loops in power systems. The AMR sensor device structure is designed to eliminate sensitivity to stray and common mode magnetic fields.

Due to the inherently low output noise of ACEINNA's sensor technology, additional filtering is not required to reduce noise that reduces accuracy at low-level currents in systems with dynamic load profiles.

The MCR1101 products in SOIC-16 package are simple to use with no or minimal external components (other than decoupling capacitor), supports high isolation and are UL/IEC/EN60950-1 certified.

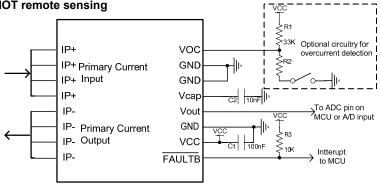


Figure 1 - Application Circuit

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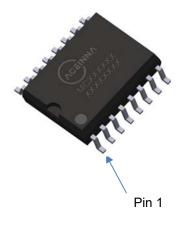
### **ORDERING PART NUMBER**

### Note: Evaluation boards are available for each product version (order EVB-MCx1101-xx-x)

Ordering PART NUMBER	Part Marking (See Page 12)	Current Range	Gain	VCC (typical)	Dielectric Strength	Package	Qty per Reel
MCR1101-5-3	MCR11053	±5 Amp	Ratiometric	3.3V	4800V	16 Lead SOIC	1000 pcs
MCR1101-20-3	MCR11203	±20 Amp	Ratiometric	3.3V	4800V	16 Lead SOIC	1000 pcs
MCR1101-50-3	MCR11503	±50 Amp	Ratiometric	3.3V	4800V	16 Lead SOIC	1000 pcs

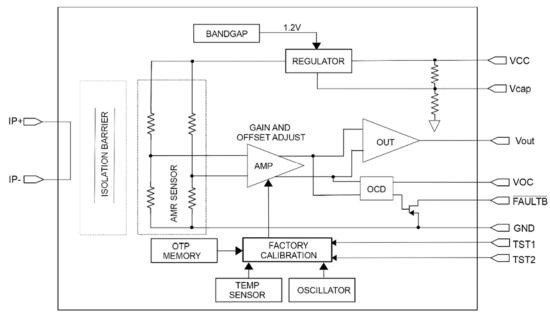
#### **PIN DESCRIPTION**

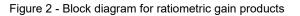
Pin # 16L SOIC	Name	Description
1,2,3,4	IP+	Input of Primary Current Path for Sensing, Fused internally
5,6,7,8	IP-	Output of Primary Current Path for Sensing, Fused internally
9	FAULTB	Overcurrent FAULTB open drain output. Active low.
10	VCC	System Power Supply
11	GND	Recommended to connect to ground
12	Vout	Analog Output Signal linearly proportional to Primary Path Current
13	Vcap	Connect 10nF capacitance to ground
14	GND	Used during initial factory calibration. This pin should be connected to ground or left floating during normal operation.
15	GND	Connect to ground
16	VOC	Input pin. Voltage on this pin defines the overcurrent detection OCD threshold level. Briefly driving this pin to VCC resets and rearms OCD circuit.



16-pin SOIC

### **BLOCK DIAGRAM**





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### Table 1 – ABSOLUTE MAXIMUM RATINGS

Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation at these or any other conditions beyond those specified is not implied.

Parameters / Test Conditions	Symbol	Value	Unit
Supply Voltage	VCC <sub>MAX</sub>	-0.5 to 6	V
FAULTB Output Voltage	V FAULTB	-0.5 to VCC+0.5V	V
Sensor Current (IP+, IP-), 5Amp products	IP <sub>MAX</sub>	±10	А
Sensor Current (IP+, IP-), 20Amp products	ІРмах	±50	А
Sensor Current (IP+, IP-), 50Amp products	ІРмах	±100	А
Maximum Device Junction Temperature	Тјмах	150	°C
Storage Temperature	Tstg	-65 to +150	°C
Operating Ambient Temperature Range	TA	-40 to 105	°C
ESD Human Body Model / per ANSI/ESDA/JEDEC JS-001	HBM	2000	V
ESD Charged Device Model / per JEDEC specification JESD22-C101	CDM	1500	V
MSL Rating	MSL	3	
Maximum Soldering Temperature, 10 seconds.	TSOLDER	260	°C

### Table 2 – ISOLATION CHARACTERISTICS

Parameters / Test Conditions	Symbol	Value	Unit
Dielectric Strength Test Voltage (Agency type-tested for 60 seconds per UL standard 60950-1 (edition 2). Production tested at 3kVrms per UL 60950-1.	Viso	4800	V
Working Voltage for Basic Isolation. Maximum approved working voltage according to UL 60950-1 (edition 2)- (V <sub>PK/DC</sub> / V <sub>RMS)</sub>	Vwvвi	1550 / 1097	V
Working Voltage for Reinforced Isolation (VPK/DC / VRMS)	Vwvri	565 / 400	V
Clearance (Minimum distance through air from IP leads to signal leads)	D <sub>CL</sub>	7.5	mm
Creepage (Minimum distance along package body from IP leads to signal leads)	D <sub>CR</sub>	8.2	mm

### Table 3 – THERMAL CHARACTERISTICS

Parameters / Test Conditions	Symbol	Value	Unit
Junction-to-Ambient Thermal Resistance(Note 1)	R <sub>0JA</sub>	27	°C/W
Junction-to-Lead Thermal Resistance	Rejc	10	°C/W

Note 1 – The  $R_{0JA}$  measured on the EB0011- evaluation board with 800mm2 of 4oz copper on each layer(top and bottom ), thermal vias connecting the layers. The performance values include the power consumed by the PCB.

# Table 4 – ELECTRICAL CHARACTERISTICS COMMON TO ALL VERSIONS

Unless otherwise noted:  $3.15V \le VCC \le 3.45V$ ,  $-40^{\circ}C \le T_A \le 105^{\circ}C$ , I (Vout) = 0 (Recommended Operating Conditions). Typical values are for VCC = 3.3V and  $T_A = 25^{\circ}C$ .

Parameter	Symbol	Test Conditions	Min	Тур	Мах	Unit		
Vout Output	Vout Output							
Load Regulation	Vout <sub>LR</sub>	Increase I (Vout) from 0 to -250µA. Measure change in Vout voltage		0.7	4	mV		
Source Current	VoutsRC	Vout shorted to GND			50	mA		
Sink Current	Vout <sub>snk</sub>	Vout shorted to VCC			30	mA		
Frequency Response (-3dB)	Vout <sub>BW</sub>	(Note 2)		1500		kHz		
Capacitive Loading	CVout <sub>MAX</sub>	(Note 2)			200	pF		
Resistive Loading	RL <sub>MIN</sub>	Minimum load resistance on Vout & Vcap. (Note 2 and Note 3)	10			kohm		
Response Time	tresp	IP± = 0 to +/-100% step input, Interval from 80% of the IP to 80% of the Vout. (Note 2)		300		ns		
Noise Density	I <sub>ND</sub>	Input Referred, VCC=3.3V, TA = 25°C, CL=200pF, DC to 100 kHz.		35		µA/√Hz		
Noise (Input Referred)	Vout <sub>NOISE</sub>	IP± = 0, Measure (Vout). DC to 100 kHz. (Note 2)		12		mA (rms)		

Note 2 – Guaranteed by design and characterization. Not production tested.

Note 3 – Vcap pin will only support capacitive loads.

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### Table 5 – ELECTRICAL CHARACTERISTICS COMMON TO ALL VERSIONS

Unless otherwise noted:  $3.15V \le VCC \le 3.45V$ ,  $-40^{\circ}C \le T_A \le 105^{\circ}C$ , I (Vout) = 0 (Recommended Operating Conditions). Typical values are for VCC = 3.3V and T<sub>A</sub>=  $25^{\circ}$ C.

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
VCC Bias Supply						
Supply Voltage	VCC		3.15		3.45	V
Supply Current	IVCC	VCC=3.3 V		4.5	6	mA
Power Up Time	TVCC	Time from VCC > 3.0V to valid Vout and Vcap (Note 2)		0.75	1.25	ms
Primary Side Input						
Primary Conductor		Measure resistance between IP+ and IP- MCR1101-50 Versions (Note 2)		0.9		
Resistance	R <sub>PC</sub>	Measure resistance between IP+ and IP- MCR1101-20, MCR1101-5 Versions (Note 2)		1.3		mΩ

Note 2 – Guaranteed by design and characterization. Not production tested. Note 3 – Vcap pin will only support Capacitive loads.

# Table 6 – PERFORMANCE CHARACTERISTICS- 50A VERSIONS (MCR1101-50-3)

Unless otherwise noted: 3.15V < VCC < 3.45V, I(Vout) = 0, Typical values are for VCC = 3.3V and T<sub>A</sub> =  $25^{\circ}C$ .

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
NOMINAL TRANSFER FUN MCR1101-50-3 Vout =	-	x 25mV/A x VCC/3.3V					
Input Range	lin	Calibrated Range	-50		+50	А	
Sensitivity	GAIN	MCR1101-50-3 (Ratiometric Gain)		25		mV/A	
DC ACCURACY							
7 0 105		I <sub>IN</sub> = 0, T <sub>A</sub> = 0°C to 85°C (Note 4)	-120	±40	120		
Zero Current Offset	IOFFSET	I <sub>IN</sub> = 0, T <sub>A</sub> = -40°C to 0°C (Note 5)	-300	±100	300	mA	
0	Es	$I_{IN} = I_{FS}$ , $T_A = 0^{\circ}C$ to 85°C (Note 4)	-1.5	±0.4	1.5	0/	
Sensitivity Error		$I_{IN} = I_{FS}$ , $T_A = -40^{\circ}C$ to 0°C (Note 5)	-2.4	±0.4	2.4	- %	
	_	$I_{IN} = I_{FS}$ , $T_A = 0^{\circ}C$ to 85°C (Note 4)	-1.5	±0.6	1.5	0/ FO	
Linearity Error	EL	$I_{IN} = I_{FS}$ , $T_A = -40^{\circ}C$ to 0°C (Note 5)	-1.5	±0.5	1.5	%FS	
<b>T</b> ( ) <b>F</b>	_	I <sub>IN</sub> = ±15A ~ ±50A, T <sub>A</sub> = 0°C to 85°C (Note 4)	-2.5	±0.7	2.5		
Total Error	Етот	I <sub>IN</sub> = ±15A ~ ±50A, T <sub>A</sub> = -40°C to 0°C (Note 5)	-3.6	±0.8	3.6	%RD	
Zero Current Offset Drift	IOFFSET(D)	(Note 6)	-300	±70	300	mA	
Sensitivity Drift	E <sub>S(D)</sub>	(Note 6)	-1.3	±0.3	1.3	%	
Total Error Drift	Etot(d)	(Note 6)	-1.7	±0.4	1.7	%FS	

Note 4: Typ values are  $1\sigma$ . Min/max values are guaranteed by production test

Note 5: Guaranteed by design and characterization. Typ values are  $1\sigma$ , min/max values are  $3\sigma$ .

Note 6: Worst case numbers are based on 3 lots qualification data, taking the worst shifts from among HTOL (1000 hours), HTSL (1000 hours), THB (1000 hours), and TCT (700 cycles). Typical numbers are 1 σ.

# Table 7 – PERFORMANCE CHARACTERISTICS- 20A VERSIONS (MCR1101-20-3)

Unless otherwise noted: 3.15V < VCC < 3.45V, I(Vout) = 0, Typical values are for VCC = 3.3V and T<sub>A</sub> =  $25^{\circ}C$ .

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
NOMINAL TRANSFER FUN MCR1101-20-3, Vout =	-	x 66mV/A x VCC/3.3V				
Input Range	lin	Calibrated Range	-20		+20	А
Sensitivity	GAIN	MCR1101-20-3 (Ratiometric Gain)		66		mV/A
DC ACCURACY					•	
7		$I_{IN} = 0$ , $T_A = 0^{\circ}C$ to $85^{\circ}C$ (Note 4)	-60	±20	60	
Zero Current Offset	IOFFSET	$I_{IN} = 0, T_A = -40^{\circ}C \text{ to } 0^{\circ}C \text{ (Note 5)}$	-200	±60	200	mA
	Es	$I_{IN} = I_{FS}$ , $T_A = 0^{\circ}C$ to 85°C (Note 4)	-0.7	±0.3	0.7	0/
Sensitivity Error		$I_{IN} = I_{FS}$ , $T_A = -40^{\circ}C$ to $0^{\circ}C$ (Note 5)	-1.2	±0.3	1.2	%
Lincovity France	-	$I_{IN} = I_{FS}$ , $T_A = 0^{\circ}C$ to 85°C (Note 4)	-0.7	±0.4	0.7	0/ 50
Linearity Error	E∟	$I_{IN} = I_{FS}$ , $T_A = -40^{\circ}C$ to $0^{\circ}C$ (Note 5)	-1.5	±0.3	1.5	%FS
	_	$I_{IN} = \pm 6A \sim \pm 20A$ , $T_A = 0^{\circ}C$ to $85^{\circ}C$ (Note 4)	-2.0	± 0.6	2.0	0/ DD
Total Error	Етот	$I_{IN} = \pm 6A \sim \pm 20A$ , $T_A = -40^{\circ}C$ to 0°C (Note 5)	-3.0	±0.8	3.0	%RD
LIFETIME DRIFT CHARACTERISTICS						
Zero Current Offset Drift	I <sub>OFFSET(D)</sub>	(Note 6)	-300	±60	300	mA
Sensitivity Drift	Es(D)	(Note 6)	-1.2	±0.3	1.2	%
Total Error Drift	Etot(d)	(Note 6)	-2.0	±0.4	2.0	%FS

Note 4: Typ values are  $1\sigma$ . Min/max values are guaranteed by production test

Note 5: Guaranteed by design and characterization. Typ values are  $1\sigma$ , min/max values are  $3\sigma$ .

Note 6: Worst case numbers are based on 3 lots qualification data, taking the worst shifts from among HTOL (1000 hours), HTSL (1000 hours), THB (1000 hours), and TCT (700 cycles). Typical numbers are 1 σ.

# Table 8 – PERFORMANCE CHARACTERISTICS- 5A VERSIONS (MCR1101-5-3)

Unless otherwise noted: 3.15V < VCC < 3.45V, I(Vout) = 0, Typical values are for VCC = 3.3V and T<sub>A</sub> =  $25^{\circ}C$ .

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
NOMINAL TRANSFER FUN MCR1101-5-3, Vout =	-	x 250mV/A x VCC/3.3V				
Input Range	lin	Calibrated Range	-5		+5	А
Sensitivity	GAIN	MCR1101-5-3 (Ratiometric Gain)		250		mV/A
DC ACCURACY					•	
7 0 10%	IOFFSET	$I_{IN} = 0, T_A = 0^{\circ}C$ to 85°C (Note 4)	-60	±20	60	
Zero Current Offset		$I_{IN} = 0, T_A = -40^{\circ}C \text{ to } 0^{\circ}C \text{ (Note 5)}$	-60	±20	60	mA
	_	$I_{IN} = I_{FS}$ , $T_A = 0^{\circ}C$ to 85°C (Note 4)	-1.0	±0.5	1.0	%
Sensitivity Error	Es	$I_{IN} = I_{FS}$ , $T_A = -40^{\circ}C$ to $0^{\circ}C$ (Note 5)	-1.5	±0.4	1.5	
	_	$I_{IN} = I_{FS}$ , $T_A = 0^{\circ}C$ to $85^{\circ}C$ (Note 4)	-0.5	±0.3	0.5	а <u>к</u> Бо
Linearity Error	E∟	$I_{IN} = I_{FS}$ , $T_A = -40^{\circ}$ C to 0°C (Note 5)	-0.75	±0.3	0.75	- %FS
	_	$I_{IN} = \pm 3A \sim \pm 5A$ , $T_A = 0^{\circ}C$ to $85^{\circ}C$ (Note 4)	-2.0	±1.3	2.0	
Total Error	Етот	$I_{IN} = \pm 3A \sim \pm 5A$ , $T_A = -40^{\circ}C$ to $0^{\circ}C$ (Note 5)	-3.0	±1.0	3.0	%RD
Zero Current Offset Drift	IOFFSET(D)	(Note 6)	-300	±70	300	mA
Sensitivity Drift	Es(D)	(Note 6)	-1.3	±0.3	1.3	%
Total Error Drift	Etot(d)	(Note 6)	-6	±1.5	6	%FS

Note 4: Typ values are  $1\sigma$ . Min/max values are guaranteed by production test

Note 5: Guaranteed by design and characterization. Typ values are  $1\sigma$ , min/max values are  $3\sigma$ .

Note 6: Worst case numbers are based on 3 lots qualification data, taking the worst shifts from among HTOL (1000 hours), HTSL (1000 hours), THB (1000 hours), and TCT (700 cycles). Typical numbers are 1 σ.

# Table 9 – OCD ELECTRICAL CHARACTERISTICS

Unless otherwise noted: 3.15V < VCC < 3.45V,  $-40^{\circ}C \le T_A \le 105^{\circ}C$ , I(Vout) = 0, Typical values are for VCC = 3.3V and  $T_A = 25^{\circ}C$ .

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
OVERCURRENT FAULT CHARACTERISTICS							
FAULTB Response Time	tresponse	Time from IP > I FAULTB to when FAULTB pin is pulled below V FAULTB ; input current step from 0 to $1.5 \times I$ FAULTB		0.2		uS	
		For parts rated for IP=5A; VOC voltage between 0 and 0.225*VCC		6			
		For parts rated for IP=5A; VOC voltage between 0.225*VCC and 0.35*VCC		7.5			
		For parts rated for IP=5A; VOC voltage between 0.35*VCC and 0.5*VCC		10		А	
FAULTB Range	I FAULTB	For parts rated for IP=20A; VOC voltage between 0 and 0.225*VCC		24			
		For parts rated for IP=20A; VOC voltage between 0.225*VCC and 0.5*VCC		30			
		For parts rated for IP=50A; VOC voltage between 0 and 0.5*VCC		60			
FAULTB Output Low Voltage	V FAULTB	In fault condition; $RF_{PU}$ = 2-10 k $\Omega$		0.2		V	
FAULTB Output High Voltage	V FAULTB	In fault condition; $RF_{PU}$ = 2-10 k $\Omega$			VCC	V	
FAULTB Pull-Up Resistance	RF <sub>PU</sub>		2		10	kΩ	
OCD Threshold Setting Error	E FAULTB			6		%	
VOC Input Range	V <sub>voc</sub>	For setting OCD trig threshold	0		VCC/2	V	
VOC high input level to reset OCD	VIHocd		VCC-0.5		VCC	V	
VOC High State Duration	THvoc		1			μs	

### AMR TECHNOLOGY

Anisotropic magnetoresistance (AMR) makes use of a common material, Permalloy, to act as a magnetometer. Permalloy is an alloy containing roughly 80% nickel and 20% iron. The alloy's resistance depends on the angle between the magnetization and the direction of current flow. In a magnetic field, magnetization rotates toward the direction of the magnetic field and the rotation angle depends on the external field's magnitude. Permalloy's resistance decreases as the direction of magnetization rotates away from the direction in which current flows, and is lowest when the magnetization is perpendicular to the direction of current flow. The resistance changes roughly as the square of the cosine of the angle between the magnetization and the direction of current flow. Permalloy is deposited on a silicon wafer and patterned as a resistive strip. The film's properties cause it to change resistance in the presence of a magnetic field. In a current sensor application, two of these resistors are connected in a Wheatstone bridge configuration to permit the measurement of the magnitude of the magnetic field produced by the current.

AMR properties are well behaved when the film's magnetic domains are aligned in the same direction. This configuration ensures high sensitivity, good repeatability, and minimal hysteresis. During fabrication, the film is deposited in a strong magnetic field that sets the preferred orientation, or "easy" axis, of the magnetization vector in the Permalloy resistors. AMR has better sensitivity than other methods and reasonably good temperature stability. The AMR sensor has sensitivity which is approximately a linear function of temperature.

#### **FUNCTIONAL DESCRIPTION**

Figure 2 provide block diagrams of the ratiometric gain. The AMR sensor monitors the magnetic field generated by the current flowing through the U shaped IP+/IP- package lead frame. The AMR sensor produces a voltage proportional to the magnetic field created by the positive or negative current in the IP+/IP- current loop while rejecting external magnetic interference. The sensor voltage is fed into a differential amplifier whose gain is temperature compensated. This is followed by an instrumentation amplifier output stage that provides a voltage that indicates the current passing through the IP+/IP- pins. To provide both positive and negative current data the Vout output pin is referenced to the ground. With no current flowing in the IP+/IP- pins, the voltage on the Vout output will typically equal the voltage of VCC/2. Positive IP+/IP- current causes the voltage on Vout to increase relative to VCC/2 while negative IP+/IP- current will cause it to decrease.

#### GAIN

The sensor resistors are biased to the VCC supply voltage and produce a differential voltage that is ratiometric to VCC. This configuration is suited to applications where the A-to-D or other circuitry receiving the current sensor output signals are biased by and ratiometric to the same supply voltage as the current sensor. The ratiometric configuration provides increased gain and resolution compared to fixed gain. The user can also provide a well-regulated 3.3V supply or monitor the VCC voltage and factor it into the current measurement to take advantage of the ratiometric configuration.

The Vout pin drives to 90% of VCC at full positive current and 10% of VCC at full negative current.

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#### **POWER UP / DOWN**

An under-voltage lockout circuit monitors the voltage on the VCC pin. If the VCC voltage is less than the under-voltage threshold the MCR1101 is in an inactive state. Vout and Vcap both drive to ground. If the VCC voltage exceeds the under-voltage threshold Vout and Vcap are released and will drive to approximately half the VCC supply voltage and an initial calibration will commence. Once the initial calibration has completed the MCR1101 becomes active. Vout will slew to indicate the value of current flowing in the IP+/- conductor. Current flow in the IP+/- conductor with a VCC voltage less than the under-voltage threshold will not cause damage to the sensor.

### **OVERCURRENT DETECTION (OCD)**

The MCR1101 have fast and accurate overcurrent fault detection circuitry. The overcurrent fault threshold (I  $_{FAULTB}$ ) is user-configurable via an external resistor divider and supports a range of 120% to 200% of the full-scale primary input (IP).

The overcurrent fault threshold (I  $_{\overline{FAULTB}}$ ) is set via a resistor divider from VCC to ground on the VOC pin. The voltage on the VOC pin (V<sub>VOC</sub>), may range from 0 ×VCC to 0.5 ×VCC.

#### For +/-5A parts

For V<sub>VOC</sub> between 0 ×VCC and 0.225 ×VCC the I  $\overline{FAULTB}$  threshold level is 1.2×IP.

For V<sub>VOC</sub> between 0.225 ×VCC and 0.35 ×VCC the I  $_{\rm FAULTB}$  threshold level is 1.5×IP.

For V<sub>VOC</sub> between 0.35 ×VCC and 0.5×VCC the I  $_{\rm FAULTB}$  threshold level is 2×IP.

For +/-20A parts

For V<sub>VOC</sub> between 0 ×VCC and 0.225 ×VCC the I  $\overline{FAULTB}$  threshold level is 1.2×IP.

For  $V_{VOC}$  between 0.225 ×VCC and 0.5 ×VCC the I  $_{\rm FAULTB}$  threshold level is 1.5×IP.

#### For +/-50A parts

For V<sub>VOC</sub> between 0 ×VCC and 0.5 ×VCC the I  $_{\overline{FAULTB}}$  threshold level is 1.2×IP.

If the input current exceeds the OCD threshold value I  $\overline{\mbox{FAULTB}}$ 

the output pin FAULTB will transition low and stay low, even if input current drops below the threshold. In order to reset the

 $\overrightarrow{\mathsf{FAULTB}}$  output the user needs to bring VOC pin to VCC and hold it there for at least THvoc. Once the OCD function is reset the VOC voltage should return back to its normal operating voltage Vvoc. A switch SW1 on Figure 1 can be used for this. Other methods are available as well.

If OCD function is used, an OCD reset must be applied to the VOC pin after system power up, to put the OCD function and  $\overline{FAULTB}$  pin in a known state.

The FAULTB output is active low open drain. A pull-up resistor should be connected between  $\overline{FAULTB}$  and VCC. The VCC voltage will determine the high level of  $\overline{FAULTB}$  signal.  $\overline{FAULTB}$  low output voltage is below 200mV. The value of pull-up resistor is 2-10kOhm.

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### **FREQUENCY RESPONSE**

The MCR1101 offers a low noise and wideband response, with a 3dB bandwidth of > 1.5MHz, as shown in the plots below.

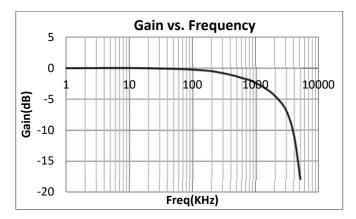


Figure 3 - Gain vs. Frequency

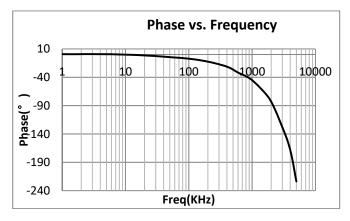
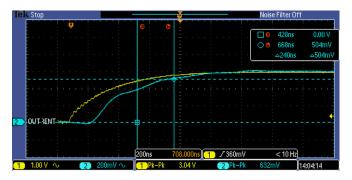
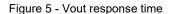


Figure 4 - Phase vs. Frequency

### **RESPONSE TIME**

Vout response time is the time interval from 80% of the IP to 80% of the Vout. The response time is 300ns typical.





### **APPLICATIONS INFORMATION**

The MCR1101 detects current by measuring the magnetic field generated by that current. Therefore it's important to consider the effect of externally generated magnetic fields, whether from another current flowing in the system, a magnet, or electromagnetic component.

In order to provide immunity to external fields, MCR1101 senses a differential field generated by the primary current, which flows through a U-shaped conductor inside the package. Therefore, to first order, the sensor will reject any common mode field originating from outside of its package.

However, it's still prudent to minimize the exposure to external fields. The MCR1101 is most sensitive to magnetic fields in the X-Y plane (i.e. the plane of the PCB surface), and is relatively insensitive to fields in the Z direction (perpendicular to the PCB surface). Thus when laying out the PCB, care should be taken to avoid a current passing directly underneath the device itself, because the magnetic field generated by that current will be parallel to the PCB surface.

When laying out the PCB, the traces carrying the input and output currents should approach the two sets of 4 input/output pins in a symmetric manner, from a direction perpendicular to the edge of the package (see Figure 6 below).

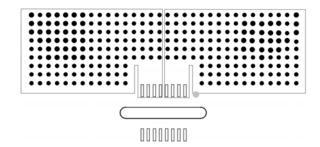


Figure 6 - Layout for current traces

#### Note:

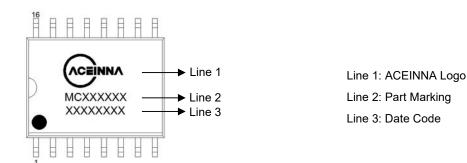
The via break in the metal at either end of the package. The purpose of these is to prevent the input current from approaching the input pins from the lateral direction

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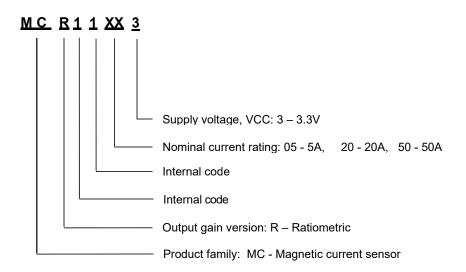
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### **DEVICE MARKING**

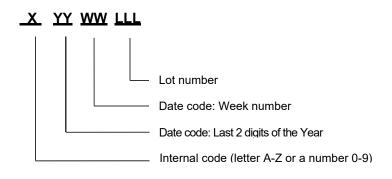
Production information is printed on the package surface by laser marking. Markings consist of 3 lines of characters including ACEINNA logo.



### PART MARKING (Line 2)

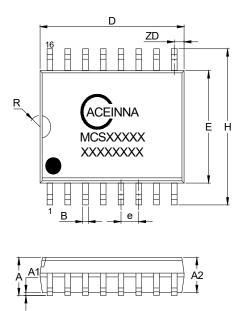


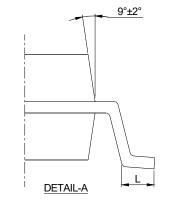
# DATE CODE (Line 3)

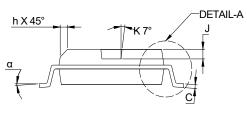


# PACKAGE OUTLINE & RECOMMENDED LAND PATTERN INFORMATION - 16-pin SOIC

# PACKAGE OUTLINE DRAWING

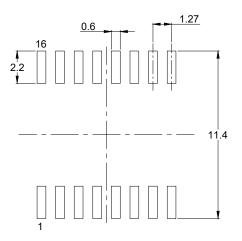






٦L	SOIC-16L	D				
SYMBOL	MILLIMETERS					
S	MIN	MAX				
А	2.44	2.64				
A1	0.10	0.30				
A2	2.24	2.44				
В	0.36	0.46				
С	0.23	0.32				
D	10.11	10.31				
Е	7.40	7.60				
е	1.27 BSC	)				
Н	10.11	10.51				
h	0.31	0.71				
J	0.53	0.73				
К	7°BSC					
L	0.51	1.01				
R	0.63	0.89				
ZD	0.66 REF					
α	0°	8°				

RECOMMENDED LAND PATTERN



#### Note:

Recommended land pattern reference IPC7351B; Adjust as necessary to meet application requirements and PCB layout tolerances.

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